NTGS3441B

[MOSFET](http://onsemi.com) – Power, Single, P-Channel, TSOP-6
-20 V, -3.5 A

Features
- Low $R_{DS(on)}$ in TSOP−6 Package
- 2.5 V Gate Rating
- This is a Pb−Free Device

Applications
- Battery Switch and Load Management Applications in Portable Equipment
- High Side Load Switch
- Portable Devices like Games and Cell Phones

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	± 8	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−3.0	A
		T_A = 70°C		−2.4	
	t ≤ 5 s	T_A = 25°C		−3.5	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.1	W
	t ≤ 5 s			1.6	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	−2.2	A
		T_A = 70°C		−1.8	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.7	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−12	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface−mounted on FR4 board using the minimum recommended pad size. (Cu area = 0.0775 in sq).
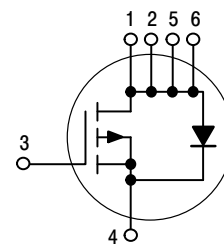
ON Semiconductor®

http://onsemi.com

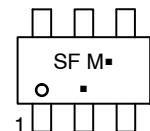| $V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
−20 V	90 mΩ @ −4.5 V	−3.0 A
	130 mΩ @ −2.5 V	−2.4 A

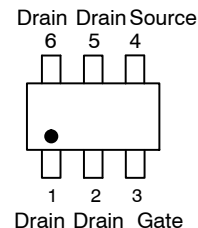**P−Channel**

MARKING DIAGRAM

TSOP−6
CASE 318G
STYLE 1

SF M▪

SF = Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT

| Drain | Drain | Source |
| 6 | 5 | 4 |

| 1 | 2 | 3 |
| Drain | Drain | Gate |

ORDERING INFORMATION

Device	Package	Shipping[†]
NTGS3441BT1G	TSOP−6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction–to–Ambient – Steady State (Note 3)	$R_{\theta JA}$	110	
Junction–to–Ambient – t ≤ 5 s (Note 3)	$R_{\theta JA}$	80	°C/W
Junction–to–Ambient – Minimum Pad (Note 4)	$R_{\theta JA}$	190	

3. Surface–mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
4. Surface–mounted on FR4 board using the minimum recommended pad size (Cu area = 0.0775 in sq).

ELECTRICAL CHARACTERISTICS ($T_J = 25°C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain–to–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ μA		−20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = -20$ V	$T_J = 25°C$			−1.0	μA
			$T_J = 70°C$			−5.0	
Gate–to–Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8$ V				± 0.1	μA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250$ μA		−0.4		−0.9	V
Drain–to–Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -3.0$ A			59	90	mΩ
		$V_{GS} = -2.5$ V, $I_D = -2.4$ A			79	130	
Forward Transconductance	g_{FS}	$V_{DS} = -10$ V, $I_D = -3.0$ A			5.8		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, f = 1 MHz, $V_{DS} = -10$ V			630		pF
Output Capacitance	C_{OSS}				93		
Reverse Transfer Capacitance	C_{RSS}				49		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5$ V, $V_{DS} = -10$ V; $I_D = -3.0$ A			6.1	9.0	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.5		
Gate–to–Source Charge	Q_{GS}				1.0		
Gate–to–Drain Charge	Q_{GD}				1.4		
SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)							
Turn–On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -1.0$ A, $R_G = 6.0$ Ω			8.0	13	ns
Rise Time	t_r				6.0	10	
Turn–Off Delay Time	$t_{d(OFF)}$				40	64	
Fall Time	t_f				33	53	
DRAIN–SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = -1.6$ A	$T_J = 25°C$		−0.8	−1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0$ V, $dI_{SD}/d_t = 100$ A/μs, $I_S = -1.6$ A			12	24	ns

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
6. Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

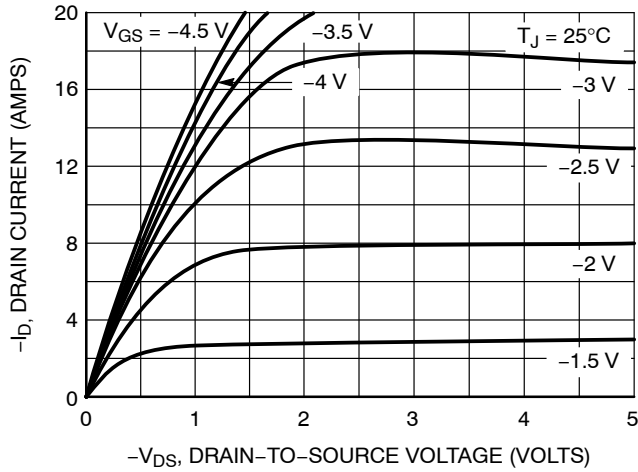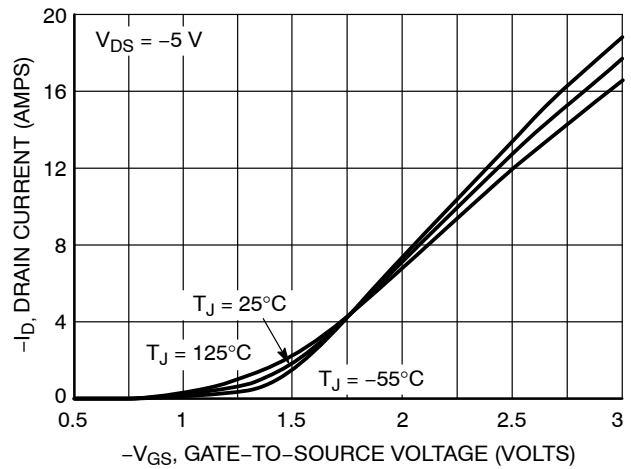**Figure 1. On−Region Characteristics**
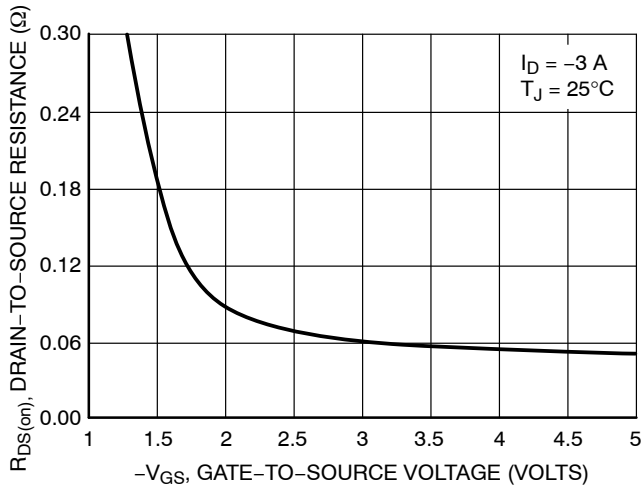
Figure 2. Transfer Characteristics

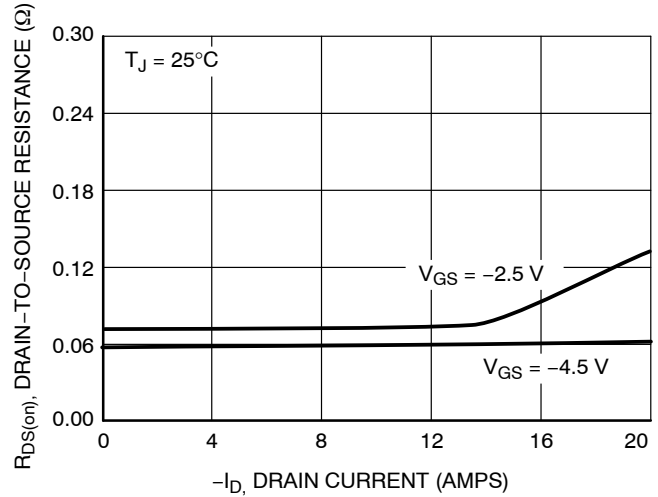**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

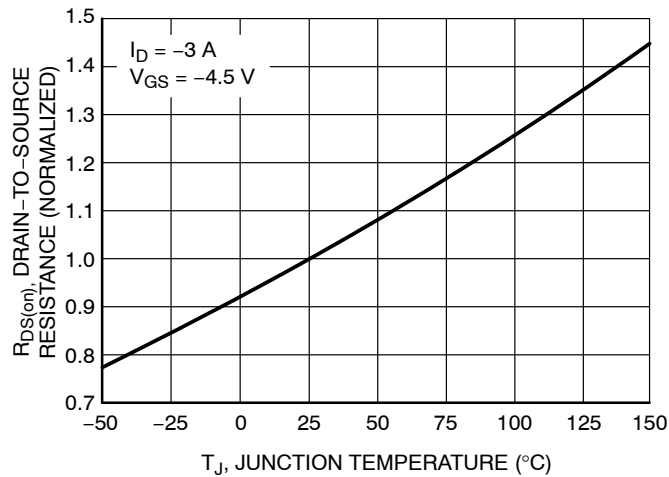**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**
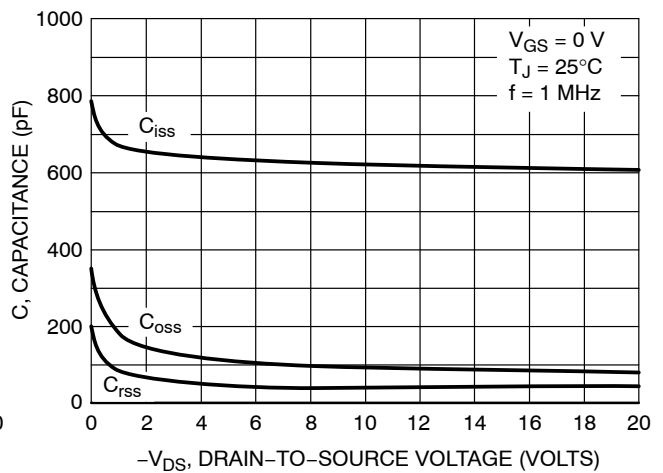
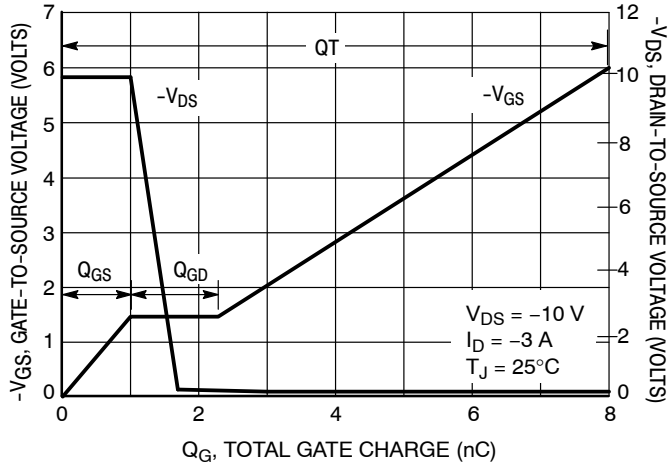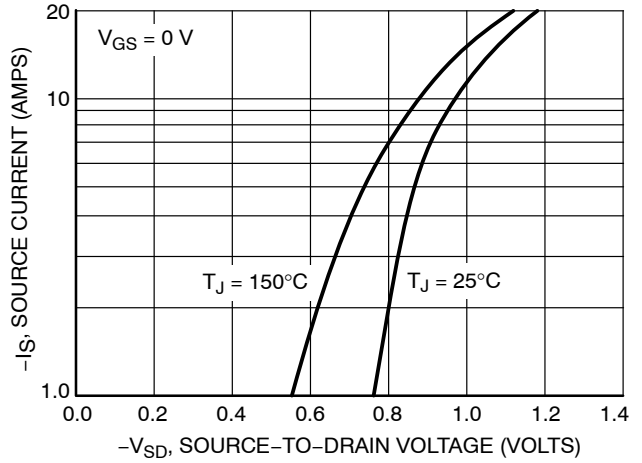**Figure 5. On−Resistance Variation with Temperature**
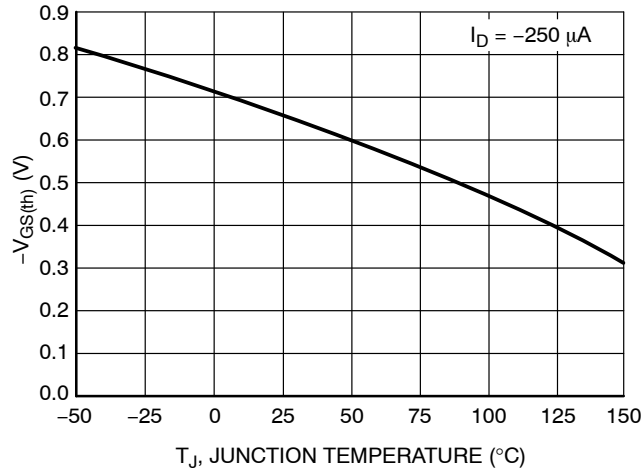
Figure 6. Capacitance Variation

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

Figure 7. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

Figure 8. Diode Forward Voltage vs. Current

Figure 9. Threshold Voltage
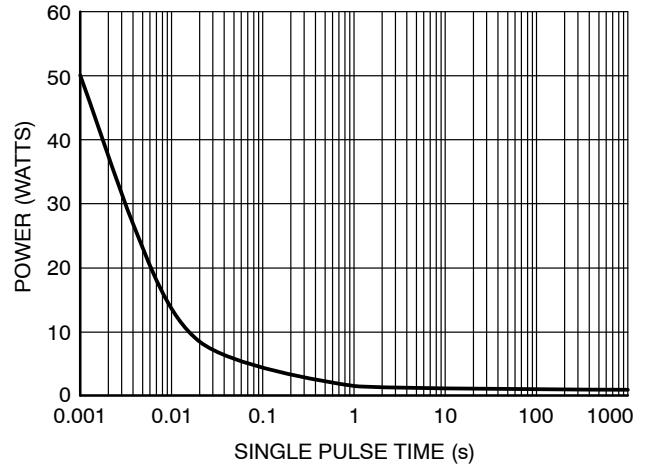
Figure 10. Single Pulse Maximum Power Dissipation
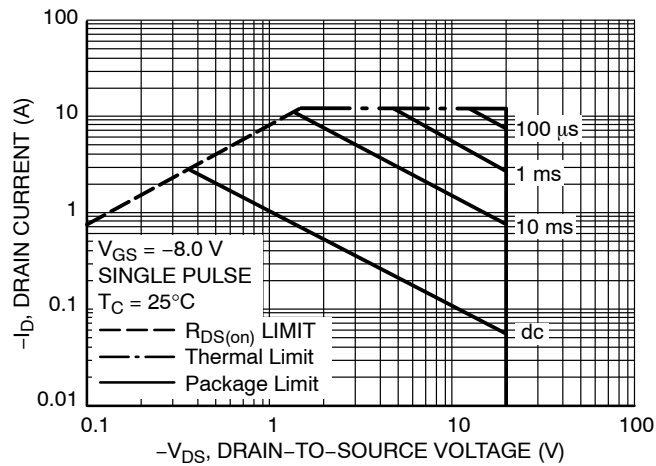
Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTGS3441B
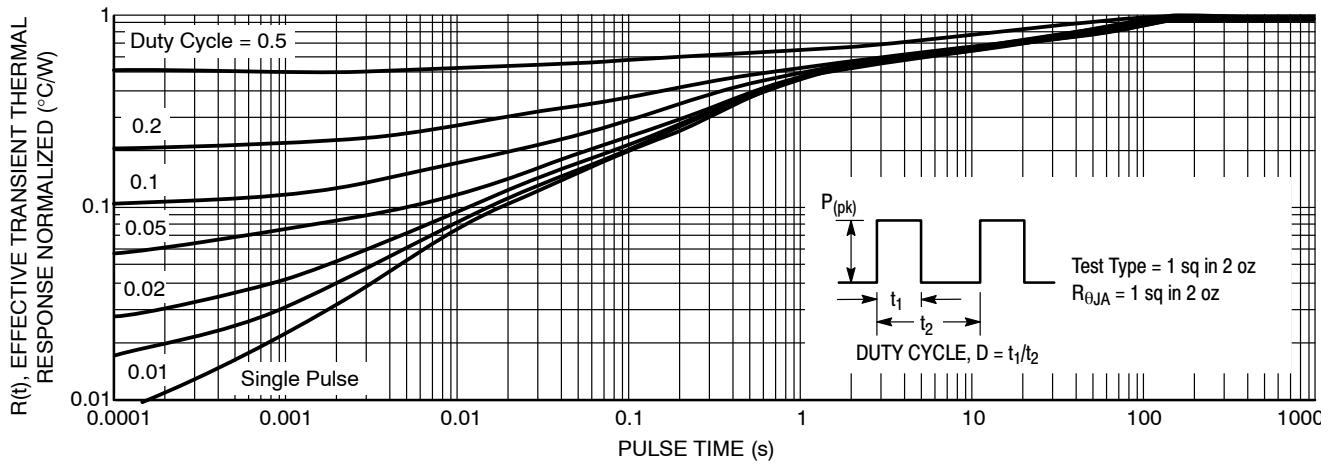
Figure 12. FET Thermal Response

**TSOP−6 3.00x1.50x0.90, 0.95P**
CASE 318G
ISSUE W

DATE 26 FEB 2024
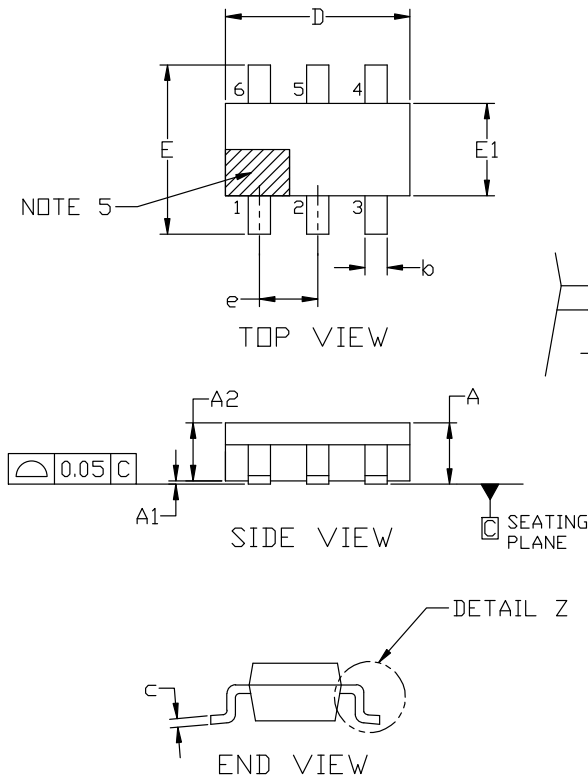
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE

TOP VIEW

SIDE VIEW

DETAIL Z
SCALE 3:1

END VIEW

DETAIL Z
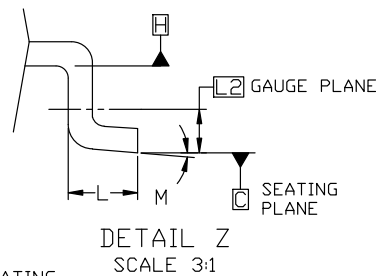
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°

6X
0.60

6X
0.95

3.20

1

0.95
PITCH
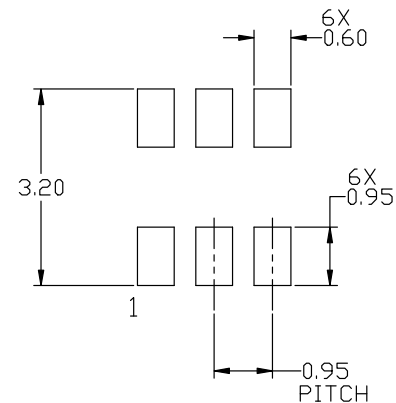
RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb−Free strategy and soldering details, please download th e ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.
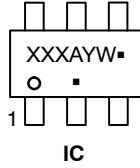
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DESCRIPTION:	TSOP−6 3.00x1.50x0.90, 0.95P		PAGE 1 OF 2

TSOP−6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

**GENERIC
MARKING DIAGRAM***

IC

XXXAYW▪

STANDARD

XXX M▪

XXX = Specific Device Code
A   = Assembly Location
Y   = Year
W   = Work Week
▪   = Pb−Free Package

XXX = Specific Device Code
M   = Date Code
▪   = Pb−Free Package

*This information is generic. Please refer to device data
sheet for actual part marking. Pb−Free indicator, "G"
or microdot "▪", may or may not be present. Some
products may not follow the Generic Marking.

STYLE 1:
PIN 1. DRAIN
    2. DRAIN
    3. GATE
    4. SOURCE
    5. DRAIN
    6. DRAIN

STYLE 2:
PIN 1. EMITTER 2
    2. BASE 1
    3. COLLECTOR 1
    4. EMITTER 1
    5. BASE 2
    6. COLLECTOR 2

STYLE 3:
PIN 1. ENABLE
    2. N/C
    3. R BOOST
    4. Vz
    5. V in
    6. V out

STYLE 4:
PIN 1. N/C
    2. V in
    3. NOT USED
    4. GROUND
    5. ENABLE
    6. LOAD

STYLE 5:
PIN 1. EMITTER 2
    2. BASE 2
    3. COLLECTOR 1
    4. EMITTER 1
    5. BASE 1
    6. COLLECTOR 2

STYLE 6:
PIN 1. COLLECTOR
    2. COLLECTOR
    3. BASE
    4. EMITTER
    5. COLLECTOR
    6. COLLECTOR

STYLE 7:
PIN 1. COLLECTOR
    2. COLLECTOR
    3. BASE
    4. N/C
    5. COLLECTOR
    6. EMITTER

STYLE 8:
PIN 1. Vbus
    2. D(in)
    3. D(in)+
    4. D(out)+
    5. D(out)
    6. GND

STYLE 9:
PIN 1. LOW VOLTAGE GATE
    2. DRAIN
    3. SOURCE
    4. DRAIN
    5. DRAIN
    6. HIGH VOLTAGE GATE

STYLE 10:
PIN 1. D(OUT)+
    2. GND
    3. D(OUT)−
    4. D(IN)−
    5. VBUS
    6. D(IN)+

STYLE 11:
PIN 1. SOURCE 1
    2. DRAIN 2
    3. DRAIN 2
    4. SOURCE 2
    5. GATE 1
    6. DRAIN 1/GATE 2

STYLE 12:
PIN 1. I/O
    2. GROUND
    3. I/O
    4. I/O
    5. VCC
    6. I/O

STYLE 13:
PIN 1. GATE 1
    2. SOURCE 2
    3. GATE 2
    4. DRAIN 2
    5. SOURCE 1
    6. DRAIN 1

STYLE 14:
PIN 1. ANODE
    2. SOURCE
    3. GATE
    4. CATHODE/DRAIN
    5. CATHODE/DRAIN
    6. CATHODE/DRAIN

STYLE 15:
PIN 1. ANODE
    2. SOURCE
    3. GATE
    4. DRAIN
    5. N/C
    6. CATHODE

STYLE 16:
PIN 1. ANODE/CATHODE
    2. BASE
    3. EMITTER
    4. COLLECTOR
    5. ANODE
    6. CATHODE

STYLE 17:
PIN 1. EMITTER
    2. BASE
    3. ANODE/CATHODE
    4. ANODE
    5. CATHODE
    6. COLLECTOR

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DESCRIPTION:	TSOP−6 3.00x1.50x0.90, 0.95P		**PAGE 2 OF 2**

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ADDITIONAL INFORMATION

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